# FS6M07652RTC
Fairchild Power Switch(FPS)

Features

- Fixed Frequency
- Internal Burst Mode Controller for Stand-by Mode
- Pulse By Pulse Over Current Limiting
- Over Current Protection(Auto Restart Mode)
- Over Voltage Protection (Auto Restart Mode)
- Over Load Protection(Auto Restart Mode)
- Internal Thermal Shutdown Function(Latch Mode)
- Under Voltage Lockout
- Internal High Voltage Sense FET
- Soft Start

Application

- LCD Monitor SMPS
- Adaptor

Description

The Fairchild Power Switch(FPS) product family is specially designed for an off line SMPS with minimal external components. The Fairchild Power Switch(FPS) consist of a high voltage power SenseFET and a current mode PWM IC. Included PWM controller features integrated fixed oscillator, the under voltage lock out, the leading edge blanking, the optimized gate turn-on/turn-off driver, the thermal shutdown protection, the over voltage protection, and the temperature compensated precision current sources for the loop compensation and a fault protection circuitry. compared with a discrete MOSFET and a controller or a RCC switching converter solution, a Fairchild Power Switch(FPS) can reduce total component count, design size, and weight and at the same time increase efficiency, productivity, and system reliability. It has a basic platform well suited for the cost effective LCD monitor power supply.

TO-220F-5L

1. Drain 2. GND 3. V_{CC}
4. Feedback 5. SoftStart
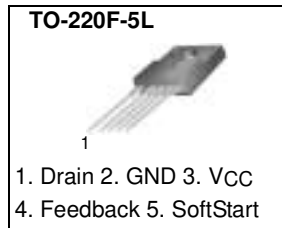
Internal Block Diagram

Rev.1.0.4
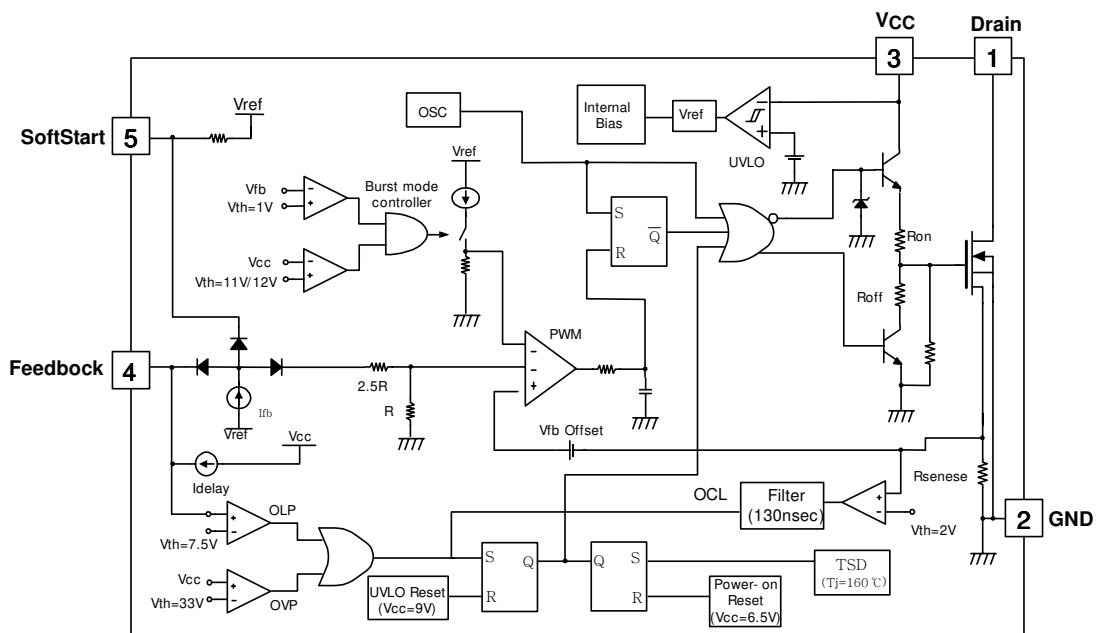
Absolute Maximum Ratings

(Ta=25°C, unless otherwise specified)

Characteristic	Symbol	Value	Unit
Drain-Gate Voltage (R_{GS}=1MΩ)	V_{DGR}	650	V
Gate-Source (GND) Voltage	V_{GS}	±30	V
Drain Current Pulsed [1]	I_{DM}	14.4	A_{DC}
Continuous Drain Current (Tc = 25°C)	I_D	3.6	A_{DC}
Continuous Drain Current (T_C=100°C)	I_D	2.28	A_{DC}
Single Pulsed Avalanche Current[3](Energy [2])	$I_{AS}(E_{AS})$	17(570)	A(mJ)
Maximum Supply Voltage	$V_{CC, MAX}$	35	V
Input Voltage Range	V_{FB}	-0.3 to V_{CC}	V
	V_{SS}	-0.3 to 10	V
Total Power Dissipation	P_D(Watt H/S)	46	W
	Darting	0.37	W/°C
Operating Junction Temperature	T_j	+150	°C
Operating Ambient Temperature	T_A	-25 to +85	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Notes:

1. Repetitive rating: Pulse width limited by maximum junction temperature
2. L=81mH, starting Tj=25°C
3. L=13uH, starting Tj=25°C

Electrical Characteristics (SFET part)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV$_{DSS}$	V$_{GS}$=0V, I$_D$=250μA	650	-	-	V
Zero Gate Voltage Drain Current	I$_{DSS}$	V$_{DS}$=650V, V$_{GS}$=0V	-	-	200	μA
		V$_{DS}$=520V V$_{GS}$=0V, T$_C$=125°C	-	-	300	μA
Static Drain-Source On Resistance [1]	R$_{DS(ON)}$	V$_{GS}$=10V, I$_D$=1.8A	-	1.3	1.6	Ω
Forward Transconductance [2]	gfs	V$_{DS}$=50V, I$_D$=1.8A	-	3.3	-	S
Input Capacitance	Ciss	V$_{GS}$=0V, V$_{DS}$=25V, f = 1MHz	-	1200	-	pF
Output Capacitance	Coss		-	125	-	pF
Reverse Transfer Capacitance	Crss		-	23	-	pF
Turn On Delay Time	td(on)	V$_{DD}$=325V, I$_D$=6.5A (MOSFET switching time is essentially independent of operating temperature)	-	22	-	nS
Rise Time	tr		-	70	-	nS
Turn Off Delay Time	td(off)		-	105	-	nS
Fall Time	tf		-	65	-	nS
Total Gate Charge (Gate-Source+Gate-Drain)	Qg	V$_{GS}$=10V, I$_D$=6.5A, V$_{DS}$=520V (MOSFET switching time is essentially independent of operating temperature)	-	40	-	nC
Gate-Source Charge	Qgs		-	6.5	-	nC
Gate-Drain (Miller) Charge	Qgd		-	18	-	nC

Note:

1. Pulse test : Pulse width ≤ 300μS, duty 2%

2. S = $\frac{1}{R}$

Electrical Characteristics (Continued)

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
UVLO SECTION						
Start Threshold Voltage	V_{START}	V_{FB} = GND	14	15	16	V
Stop Threshold Voltage	V_{STOP}	V_{FB} = GND	8	9	10	V
OSCILLATOR SECTION						
Initial Frequency	F_{OSC}	-	63	70	77	kHz
Voltage Stability	F_{STABLE}	12V ≤ V_{CC} ≤ 23V	0	1	3	%
Temperature Stability (2)	ΔF_{OSC}	-25°C ≤ Ta ≤ 85°C	0	±5	±10	%
Maximum Duty Cycle	D_{MAX}	-	75	80	85	%
Minimum Duty Cycle	D_{MIN}	-	-	-	0	%
FEEDBACK SECTION						
Feedback Source Current	I_{FB}	V_{FB} = GND	0.7	0.9	1.1	mA
Shutdown Feedback Voltage	V_{SD}	V_{FB} ≥ 6.9V	6.9	7.5	8.1	V
Shutdown Delay Current	I_{DELAY}	V_{FB} = 5V	3.2	4.0	4.8	μA
SOFTSTART SECTION						
Softstart Voltage	V_{SS}	V_{FB} = 2	4.7	5.0	5.3	V
Softstart Current	I_{SS}	V_{SS} = V	0.8	1.0	1.2	mA
BURST MODE SECTION						
Burst Mode Low Threshold Voltage	V_{BURL}	V_{FB} = 0V	10.4	11.0	11.6	V
Burst Mode High Threshold Voltage	V_{BURH}	V_{FB} = 0V	11.4	12.0	12.6	V
Burst Mode Enable Feedback Voltage	V_{BEN}	V_{CC} = 10.5V	0.7	1.0	1.3	V
Burst Mode Peak Current Limit (4)	I_{BURPK}	V_{CC} = 10.5V, V_{FB} = 0V	0.38	0.5	0.62	A
Burst Mode Frequency	F_{BUR}	V_{CC} = 10.5V, V_{FB} = 0V	63	70	77	kHz
CURRENT LIMIT(SELF-PROTECTION)SECTION						
Peak Current Limit (4)	I_{OVER}	-	1.76	2.0	2.24	A
PROTECTION SECTION						
Over Voltage Protection	V_{OVP}	V_{CC} ≥ 29V	29	33	37	V
Over Current Latch Voltage (3)	V_{OCL}	-	1.8	2.0	2.2	V
Thermal Shutdown Temp (2)	T_{SD}	-	140	160	-	°C
TOTAL DEVICE SECTION						
Start Up Current	I_{START}	V_{FB} = GND, V_{CC} = 14V	-	0.1	0.17	mA
Operating Supply Current (1)	I_{OP}	V_{FB} = GND, V_{CC} = 16V	-	10	15	mA
	$I_{OP(MIN)}$	V_{FB} = GND, V_{CC} = 12V				
	$I_{OP(MAX)}$	V_{FB} = GND, V_{CC} = 30V				

Notes:

1. These parameters are the current flowing in the control IC.
2. These parameters, although guaranteed at the design, are not 100% tested in production.
3. These parameters, although guaranteed, are tested in EDS(wafer test) process.
4. These parameters indicate inductor current.
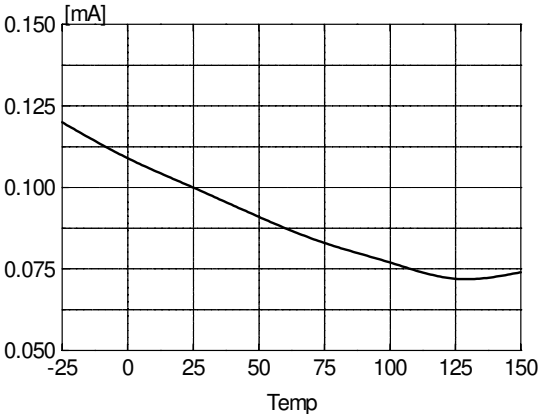
Typical Performance Characteristics

[mA]

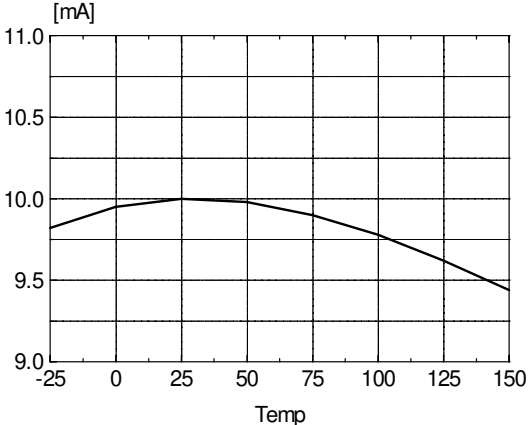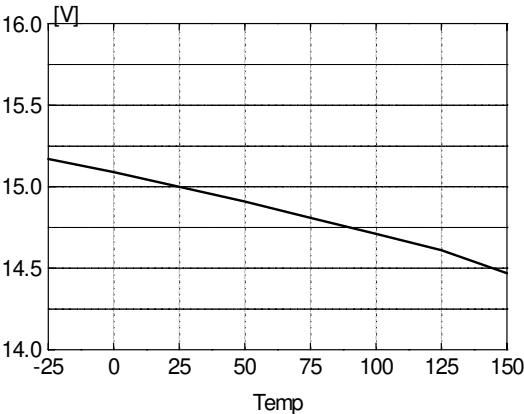Figure 1. Start Up Current vs. Temp

Figure 2. Operating Current vs. Temp
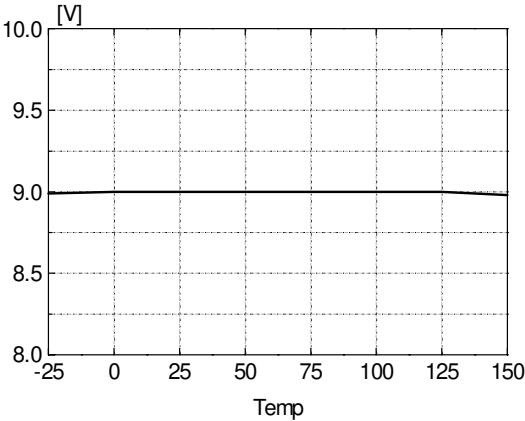
Figure 3. Start Threshold Voltage vs. Temp

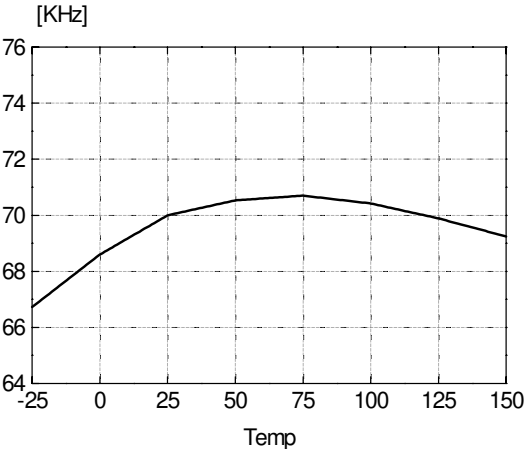Figure 4. Stop Threshold Voltage vs. Temp
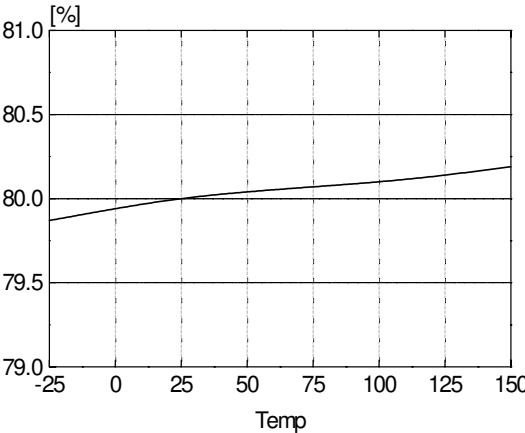
Figure 5. Initial Freqency vs. Temp

Figure 6. Maximum Duty vs. Temp

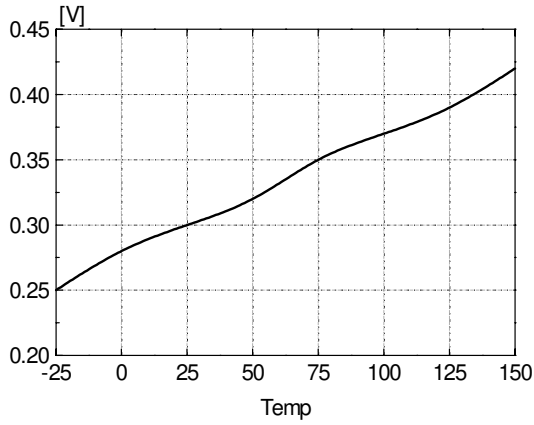# Typical Performance Characteristics (Continued)
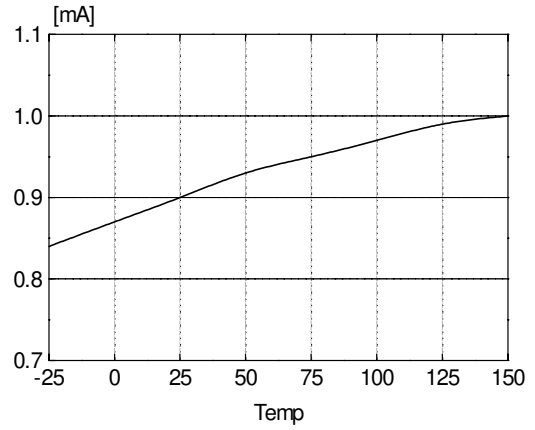
Figure 7. Feedback Offset Voltage vs. Temp

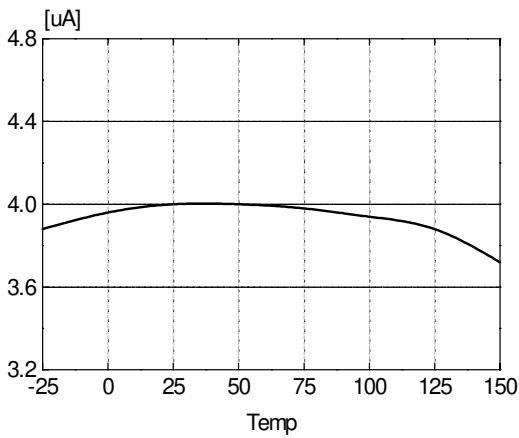**Figure 8. Feedback Source Current vs. Temp**
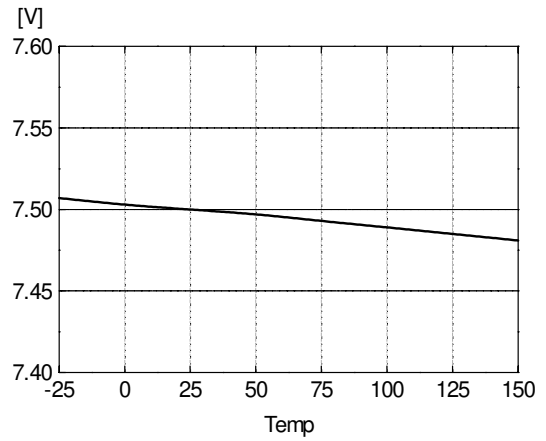
Figure 9. ShutDown Delay Current vs. Temp

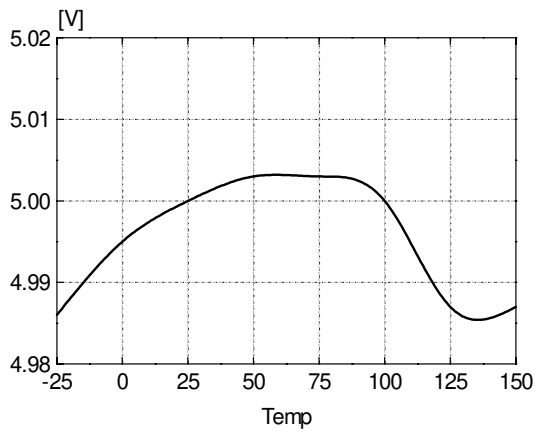**Figure 10. ShutDown Feedback Voltage vs. Temp**

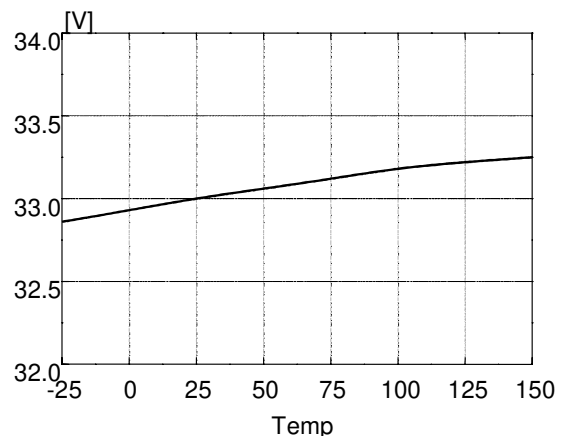**Figure 11. Softstart Voltage vs. Temp**

Figure 12. Over Voltage Protection vs. Temp

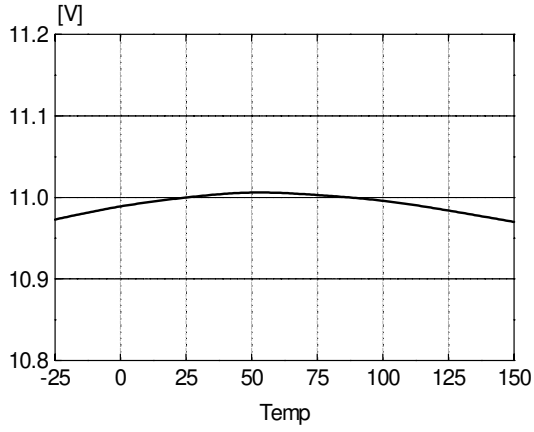# Typical Performance Characteristics (Continued)

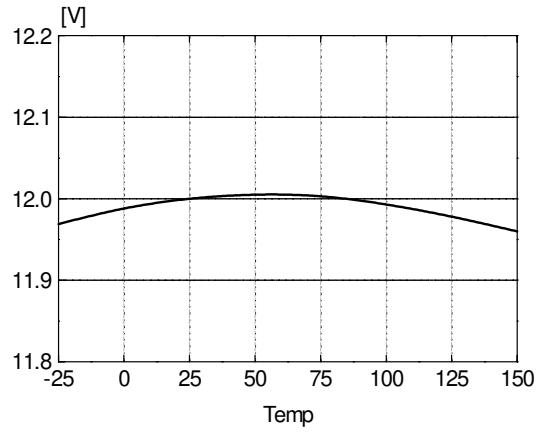

Figure 13. Burst Mode Low Voltage vs. Temp

Figure 14. Burst Mode High Voltage vs. Temp
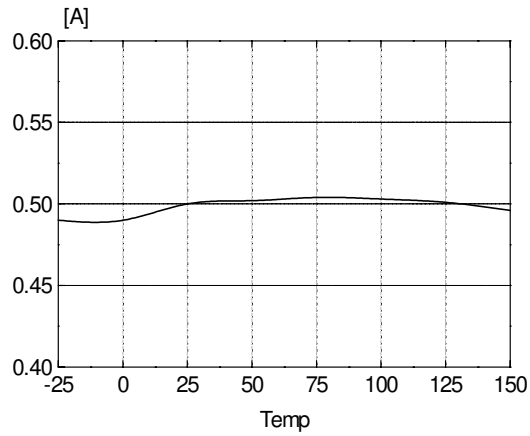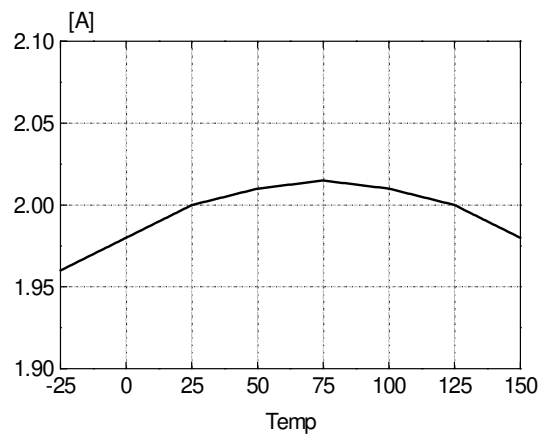

Figure 15. Burst Mode Peak Current vs. Temp

Figure 16. Over Current Limit vs. Temp

Package Dimensions

TO-220F-5L
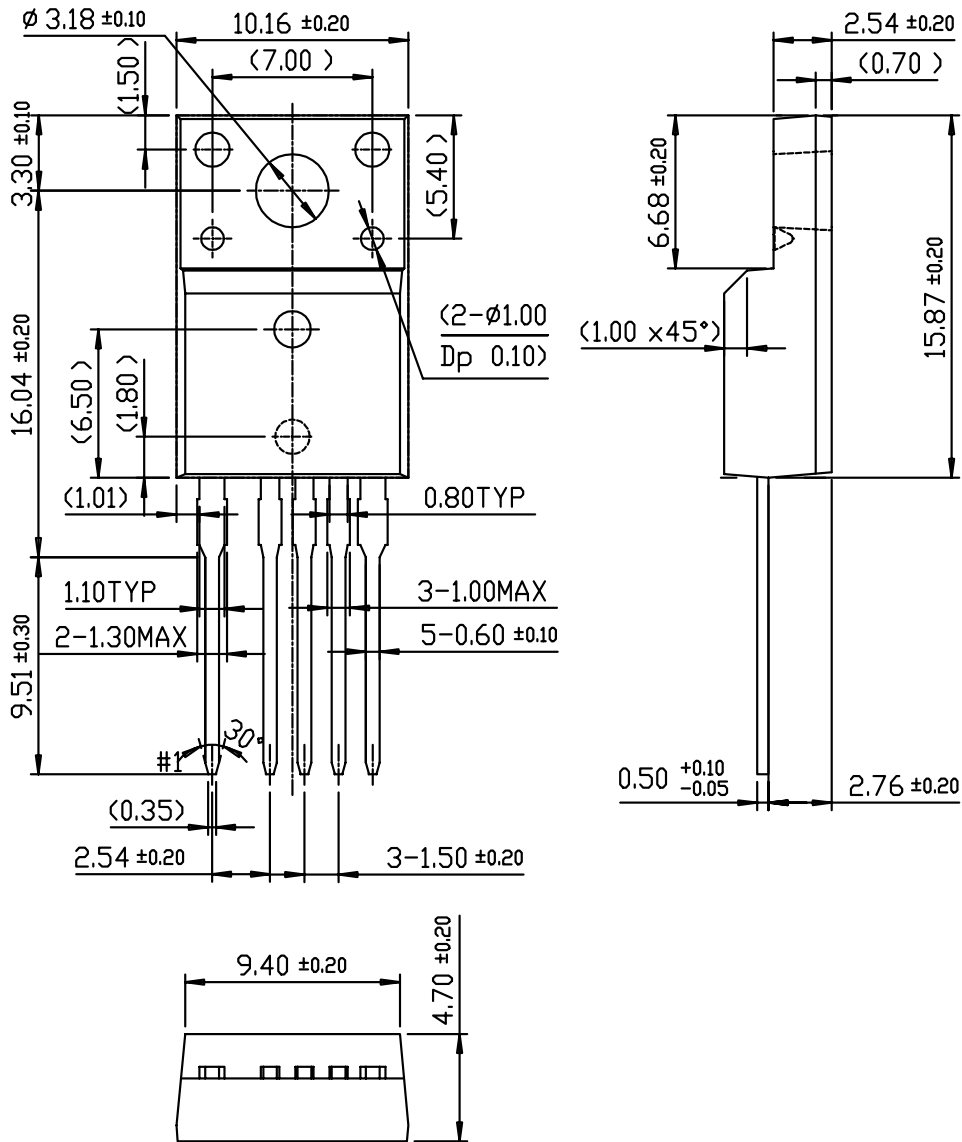
Package Dimensions (Continued)

TO-220F-5L(Forming)

Ø 3.18 ±0.10

10.16 ±0.20

(7.00)

(1.50)

(5.40)

15.87 ±0.20

3.30 ±0.10

(6.50)

(1.80)

(2-Ø1.00
Dp 0.10)

10.63 ±0.50

(1.01)

1.10TYP

2-1.30MAX
(#1,#5)

0.80TYP

3-1.00MAX
(#2,#3,#4)

#1   #5

5-0.60 ±0.10

2.54TYP
[2.54±0.20]

3-1.50TYP
[3-1.50±0.20]

9.40 ±0.20

4.70 ±0.20

2.54 ±0.20

(0.70)

6.68 ±0.20

16.08

(1.00 ×45°)

18.20 ±0.50

(3.50)

5.63 ±0.50

5.00 ±0.50

2.76 ±0.30

(#2,#4)   (#1,#3,#5)

0.50 +0.10 −0.05

3.18 ±0.30
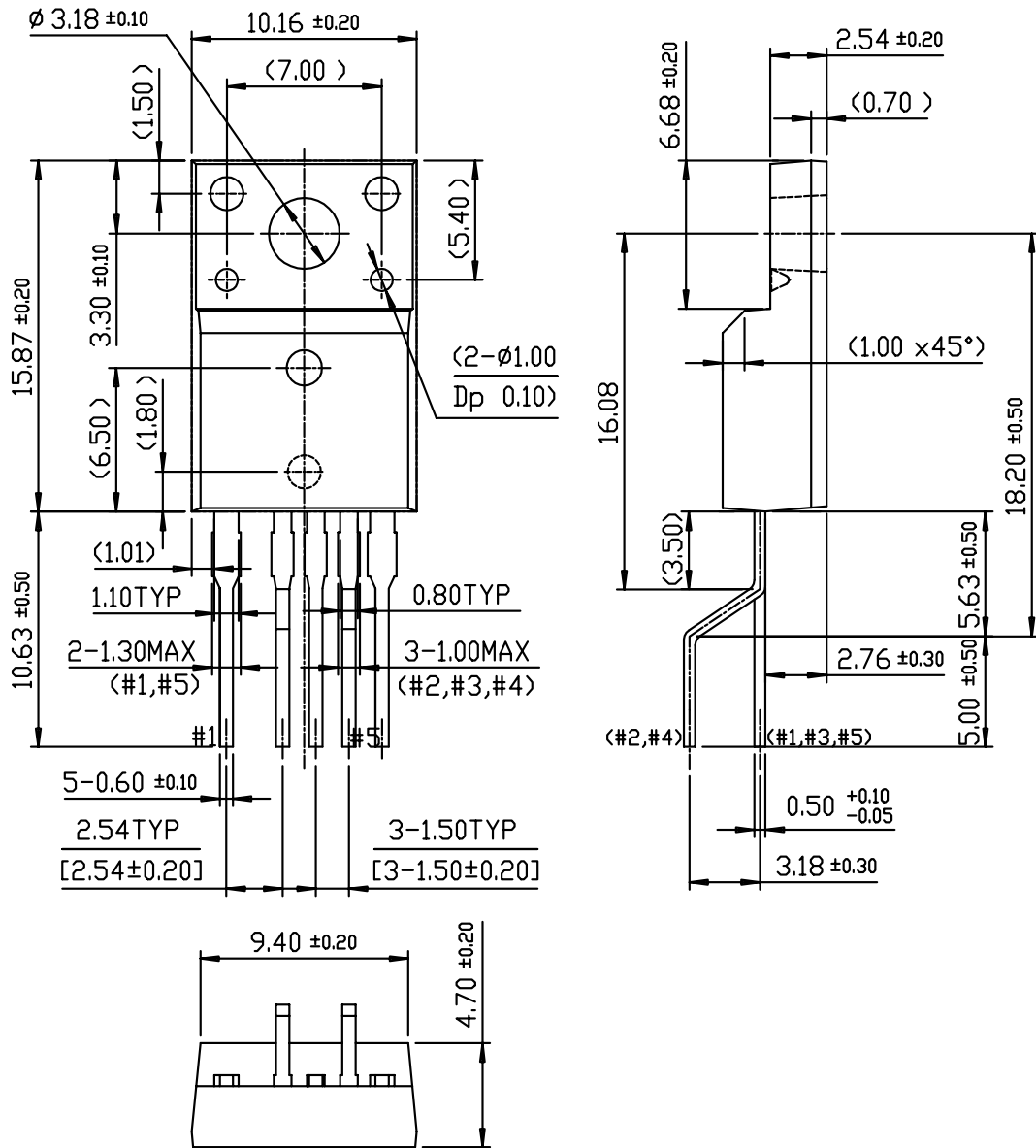
Ordering Information

Product Number	Package	Marking Code	BVdss	Rds(on)
FS6M07652RTCTU	TO-220F-5L	6M07652R C	650V	1.6
FS6M07652RTCYDT	TO-220F-5L(Forming)			

TU : Non Forming Type

YDT : Forming Type

DISCLAIMER
FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY
PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY
LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER
DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY
FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES
OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF FAIRCHILD SEMICONDUCTOR
CORPORATION. As used herein:

1. Life support devices or systems are devices or systems
   which, (a) are intended for surgical implant into the body,
   or (b) support or sustain life, and (c) whose failure to
   perform when properly used in accordance with
   instructions for use provided in the labeling, can be
   reasonably expected to result in a significant injury of the
   user.

2. A critical component in any component of a life support
   device or system whose failure to perform can be
   reasonably expected to cause the failure of the life support
   device or system, or to affect its safety or effectiveness.

www.fairchildsemi.com